

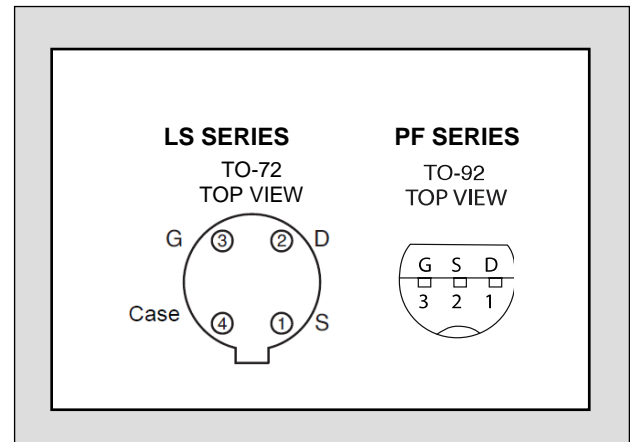
LINEAR SYSTEMS

Twenty-Five Years Of Quality Through Innovation

LS5301, PF5301

VERY HIGH INPUT IMPEDANCE
N-CHANNEL JFET

FEATURES	
REPLACEMENT FOR LF5301, PF5301	
HIGH INPUT INPEDANCE	$I_G = 0.100 \mu\text{A}$
HIGH GAIN	$g_{fs} = 70 \mu\text{S}$
ABSOLUTE MAXIMUM RATINGS ¹	
@ 25 °C (unless otherwise stated), $T_A = 25^\circ\text{C}$	
Maximum Temperatures	
Storage Temperature (TO-72)	-55 to 175°C
Storage Temperature (TO-92)	-55 to 150°C
Maximum Power Dissipation ²	
Continuous Power Dissipation), $T_A = 25^\circ\text{C}$	300mW
Maximum Currents	
Gate Current	50mA
Maximum Voltages	
Gate to Drain	-30V
Gate to Source	-30V



COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNIT	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	-30			V	$V_{DS} = 0V, I_D = -1\mu\text{A}$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-0.6		-3.0		$V_{DS} = 10V, I_D = 1nA$
I_{GSS}	Gate Leakage Current			-1	pA	$V_{DS} = 0V, V_{GS} = -15V$
I_G	Gate Operating Current		-0.04			$V_{DG} = 6V, I_D = 5\mu\text{A}$
I_{DSS}	Drain to Source Saturation Current	30		500	μA	$V_{DS} = 10V, V_{GS} = 0V$
g_{fs}	Forward Transconductance	70		300	μS	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{kHz}$
C_{iss}	Input Capacitance			3	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{MHz}$
C_{riss}	Reverse Transfer Capacitance			1.5		
e_n	Equivalent Noise Voltage		45	150	nV/ $\sqrt{\text{Hz}}$	$V_{DG} = 10V, I_D = 50\mu\text{A}, f = 100\text{Hz}$

NOTES

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Derate PF series 2.8mW/°C when $T_A > 25^\circ\text{C}$. Derate LS series 2.0mW/°C when $T_A > 25^\circ\text{C}$
3. All MIN/TYP/MAX limits are absolute numbers. Negative signs indicated electrical polarity only.

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Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, co-founder and vice president of R&D at Intersil, and founder/president of Micro Power Systems.

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